

REMARKS

Entry of this amendment is respectfully requested prior to examination of the application.

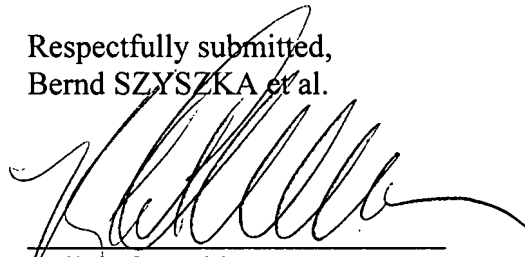
Applicant notes that claims have been amended strictly to ensure closer compliance with U.S. patent practice and not for a reason related to patentability or for a reason related to distinguishing the invention over any known prior art reference. Accordingly, Applicant submits that no estoppel should apply to any feature recited in any of the so amended claims.

Additionally, the specification and abstract have been amended to ensure closer compliance with U.S. patent practice. Applicant submits that the amendments to the claims, specification, and abstract do not introduce new matter.

Authorization is hereby given to charge any fees necessary for the consideration of this preliminary amendment to deposit account No. 19-0089.

Should the Examiner have any further comments or questions, the Examiner is invited to contact the undersigned at the below-listed telephone number.

Respectfully submitted,
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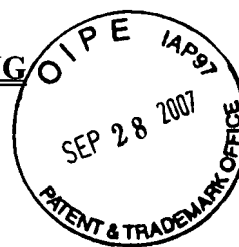
September 19, 2007
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METHOD AND DEVICE FOR MAGNETRON SPUTTERING

~~Method and Device for Magnetron Sputtering~~

~~Applicant:~~

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**CROSS REFERENCE TO RELATED APPLICATIONS**

[0001] This application is a National Stage entry under 35 U.S.C. §371 of International Application PCT/EP2004/013532, which was filed on November 29, 2004, the disclosure of which is expressly incorporated by reference herein in its entirety. Moreover, this application claims priority to German Patent Application No. DE 103 59 508.2-45.

BACKGROUND OF THE INVENTION

1. Field of the Invention

[0002] The invention relates to a method and a device for magnetron sputtering. These technologies are used for depositing functional and finishing layers. Magnetron sputtering technologies are already used on a large scale in industrial production, e.g., for coating architectural glass.

2. Discussion of Background Information

[0003] Coating processes in which the coating is composed of several chemical elements, e.g., titanium dioxide, are of particular technical importance. ~~Titanium dioxide is one example.~~ With coating processes of this type, the metallic component is often provided by sputtering a metallic target. The other layer component is introduced into the process chamber in a gaseous form. High coating rates and optimal layer quality can only be achieved with these ~~so-called~~ reactive coating processes ~~only~~ when the process is operated in the area of unstable operating points (i.e., in the transition mode). This ~~so-called~~ transition mode is characterized in that the reactive gas feed ~~on the one hand~~ is large enough to provide a sufficient amount of reactive gas for the layer deposit. ~~On the other hand, however, the~~

~~amount of reactive gas fed is~~ while at the same time being so low that a contamination of the sputter target with reactive gas is avoided. Particularly with these unstable operating points, constant quality and reproducibility of the coating require the magnetron sputtering system to be operated with the aid of complex control loops.

[0004] According to the prior art, magnetron sputtering sources can be influenced through the electric power fed or the reactive gas flow. The necessary control signal can be obtained by measuring different parameters. Thus, for example, it is proposed in EP 1 232 293 B1 to use the harmonic content of the electric parameters of the discharge as a control variable.

[0005] ~~It~~ Additionally, it is known from EP 0 795 623 A1 to determine the partial pressure of reactive gases with suitable probes. Thus, for example, the oxygen partial pressure measured with a lambda probe can be used as a control variable. ~~It~~ Also, it is known from J. Affinito et al., J. Vac. Sci. Technol. A 2 (1984), p. 1275-1284, to control a magnetron sputtering source by measuring the plasma impedance. As a further possibility, the dissertation by J. Strümpfel, *Prozessstabilisierung beim reaktiven Hochratenzerstäuben mittels optischer Emissionsspektroskopie zur industriellen Herstellung von Indium-Zinn-Oxidschichten und Titandioxidschichten*, Chemnitz 1991, describes the measurement of the intensity of selected spectral lines of the plasma of the magnetron sputtering sources.

[0006] Furthermore, the deposition rate of a magnetron sputtering source that is operated in the unstable transition range is not absolutely known. ~~The~~ As such, the layer thicknesses of the layers produced on the substrate ~~therefore~~ have to be determined after deposition. Optical measurements such as photometry or ellipsometry are primarily used to this end.

[0007] The described expenditure in terms of equipment for each individual sputtering source of a coating system is necessary in order to ensure a constant layer quality, a constant layer structure and a constant layer thickness. This results ~~on the one hand~~ in high costs in acquiring and operating the coating system, as well as in a high susceptibility to damage. ~~This applies in particular to,~~ particularly in large in-line systems.

[0008] The coating of steel band substrates or architectural glass is carried out in continuous process on an industrial scale with in-line systems of this type. Such coating systems have a large number of magnetron sputtering sources. Twenty to ~~approx.~~ approximately thirty sources are typical ~~hereby~~; however, systems with up to sixty magnetron sputtering sources

are also in use. ~~What~~ Accordingly, what is critical for industrial production is ~~thereby~~ the interaction of all of these individual sputtering sources, whereby several sources often deposit one and the same material. Only through very great expenditure is it ~~thereby~~ possible for all the sources to supply identical results with respect to layer properties, coating rate and homogeneity.

[0009] An optical measurement of the layer properties after each sputtering source has proven to be extraordinarily difficult. Such methods are inapplicable in practice with overall systems having a plurality of optical measuring systems due to high costs and high susceptibility to damage. ~~In addition to high costs, in particular the high susceptibility to damage of this overall system, which has a plurality of optical measuring systems, makes such methods inapplicable in practice.~~

SUMMARY OF THE INVENTION

[0010] ~~The object of~~ Accordingly, the invention is ~~therefore directed to disclose~~ a sputtering source which, without monitoring of the deposited layer and without complex control loops, makes it possible to deposit layers with defined properties and with defined coating rates. Furthermore, the ~~object invention~~ is directed to disclose a sputtering source that has a higher coating rate compared to the prior art for high-refractive materials such as titanium dioxide.

[0011] ~~The object is attained through~~ In embodiments, there is a magnetron coating system including a first coating source, an auxiliary substrate arranged between the first coating source and an area that is provided for receiving a substrate to be coated, and a magnetron. The auxiliary substrate forms a cathode for this magnetron. Moreover, a device for determining the area density of the auxiliary substrate is included. In additional embodiments, the invention is directed to a method for depositing thin layers, in which a layer is deposited on an auxiliary substrate by a first coating source, the auxiliary substrate is used as a cathode for coating a substrate by a magnetron, and the area density of the auxiliary substrate is determined. ~~according to independent claim one and a method for depositing thin layers according to independent claim seven. Preferred embodiments are found in the respective dependent claims.~~

[0012] ~~The~~ A magnetron coating system according to embodiments the invention comprises a first coating source, an auxiliary substrate, which is arranged between this first coating source and the area which is provided to receive the substrate to be coated, and a magnetron. ~~Means are thereby~~ A device is provided for determining the area density of this auxiliary substrate, and the auxiliary substrate forms a cathode for the referenced magnetron.

[0013] ~~To~~ In implementations, to deposit a layer on a substrate, initially ~~accordingly~~ first a layer is deposited with known deposit rate by ~~means of~~ the first coating source onto an auxiliary substrate. This auxiliary substrate now serves as a sputtering cathode for coating the substrate by ~~means of~~ the magnetron. Of course, not only the layer deposited on the auxiliary substrate can ~~thereby~~ be removed, but also the material of the auxiliary substrate itself. In this case, both materials, optionally together with a component fed in a gaseous form, form the final layer on the substrate.

[0014] ~~After~~ In further embodiments, after the determination of the area density of the auxiliary substrate, the area density of the substrate can be determined from the mass balance of the auxiliary substrate. ~~For~~ The first coating source may comprise, for example, a planar magnetron, a linear ion source, which sputters a target or implants xenon or krypton, a linear source that is based on the principle of laser ablation, or a linear evaporation source is suitable as the first coating source.

[0015] ~~The~~ In even further embodiments, the auxiliary substrate is preferably embodied as a rotating, cylindrical body. Those areas that are facing the first coating source can thus be provided with a coating continuously, while at the same time those area elements that are facing the substrate are continuously available as a sputtering cathode for coating the substrate. The auxiliary substrate is thus a component of a rod cathode magnetron. The cylindrical auxiliary substrate can be hollow in the interior area ~~and thus (i.e., tubular)~~, or embodied as a solid rod. The material sputtered off by the first magnetron can be continuously transported to the substrate and deposited there through the rotation of the auxiliary substrate.

[0016] In a particularly advantageous embodiment, the first coating source is a planar magnetron. This first magnetron is thereby operated in a pure inert atmosphere. The coating rate can thus be determined absolutely from the known sputtering rate and from the electric discharge parameters.

[0017] ~~If now~~ When the second magnetron is operated with reactive gas or a mixture of inert and reactive gas, the coating rate of the substrate can be only inadequately quantified due to the constantly changing reactive gas partial pressure at this point. ~~After~~ However, after the determination of the area density on the auxiliary substrate, ~~however,~~ the coating rate of the substrate can be determined absolutely from the mass balance of the auxiliary substrate.

[0018] ~~From ease to ease~~ In selected embodiments, the first coating source can be arranged in a shield in order to prevent the penetration of reactive gas components which would contaminate the coating source.

[0019] ~~Advantageously~~ According to further aspects of the invention, the area density of the auxiliary substrate is determined by means of x-ray fluorescence. Overall, in this manner, the coating rate of the substrate can be determined with an error of less than 0.1%.

[0020] ~~Argon~~ In embodiments, argon in particular is suitable as inert gas for operating the first magnetron. ~~This is, such implementations being~~ available without major technical effort and at low cost. Moreover, argon as an inert gas has a high ionization potential and remains inert even at high temperatures. ~~Nitrogen and/or~~ Additionally, at least one of nitrogen, oxygen, and and/or methane in particular are suitable as a reactive gas. Thus, in combination with a metallic sputter target nitrides, oxides or carbides can be deposited as a thin layer on the substrate.

[0021] In embodiments, the metallic target comprises particular a metal layer of less than 100 nanometers, ~~particularly~~ preferably a layer of less than 10 nanometers thick, deposited on the auxiliary substrate ~~is suitable as a metallic target~~. It is known from S. Berg, J. Vac. Sci. Technol. A 10 (1992), p. 1592-1596, that the sputtering rate of materials with implanted heavy atoms is clearly higher compared to the sputtering rate of the pure material. Thus, with the magnetron coating system according to aspects of the invention, high deposition rates can be achieved even with operating conditions outside the transition mode. For materials with a high refractive index, such as, e.g., titanium dioxide, the device according to aspects of the invention allows the coating rate to increase by more than 50%.

[0022] ~~A~~ In implementations, a particularly high increase in the coating rate results ~~accordingly~~ when the metal layer deposited by ~~means of~~ the first magnetron has a higher mass number than the average mass number of the material of the auxiliary substrate. Thus, for

example, the sputtering rate of a 2 nm thick layer of tungsten on an auxiliary substrate of aluminum is greater (e.g., by up to a factor of 3) than the sputtering rate of a homogenous tungsten target.

[0023] ~~As is known from the prior art,~~ In embodiments, the second magnetron can be operated as an individual magnetron with DC voltage or with pulsed DC voltage. Advantageously, ~~however, the a device according to a particular embodiment of the invention is operated as a double magnetron with an AC voltage of approx. approximately 10 kHz to approx. approximately 100 kHz.~~ Operation, at a frequency of 40 kHz ~~is particularly advantageous.~~ With such operation as a double magnetron, two of the arrangements shown in Fig. 1 are connected to the poles of an AC source. Each auxiliary substrate is thus alternately switched as anode and cathode. An effective unification of the surfaces of the auxiliary substrates occurs through the alternating electron bombardment of the auxiliary substrates. This increases the process stability as desired. Furthermore, the operation of at least two auxiliary substrates as a double magnetron leads to a greater plasma density and thus to improved layer properties as desired.

[0024] The magnetron coating system according to the invention thus makes it possible for the first time to monitor the achievement of a predetermined layer thickness in a simple manner with the aid of the integral measuring technique. With the aid of this technology, even large in-line sputtering systems with a plurality of coating stations can be realized, which were not manageable with the control methods and optical diagnosis systems hitherto available.

[0025] According to a first aspect of the invention, there is a magnetron coating system comprising a first coating source and an auxiliary substrate arranged between the first coating source and an area into which a substrate to be coated is to be received. The system also includes a magnetron having a cathode composed of the auxiliary substrate and a device structured and arranged to determine an area density of the auxiliary substrate.

[0026] In embodiments, the auxiliary substrate is formed as a cylinder, and the magnetron comprises a rod cathode magnetron. Additionally, the first coating source may comprise a planar magnetron and a shield. Moreover, the device may comprise a detection device structured and arranged to determine x-ray fluorescence. Even further, the system may

comprise additional auxiliary substrates, wherein the magnetron comprises additional cathodes composed of the additional auxiliary substrates.

[0027] According to a second aspect of the invention, there is a method for depositing thin layers. the method includes depositing a layer on an auxiliary substrate via a first coating source, coating a substrate via a magnetron having a cathode composed of the auxiliary substrate, and determining an area density of the auxiliary substrate.

[0028] In embodiments, a thickness of the layer deposited on the auxiliary substrate is less than 100 nm, and preferably less than 10 nm. Furthermore, the layer deposited on the auxiliary substrate may comprise a metal layer, such as an element having a higher mass number than an average mass number of a material of the auxiliary substrate.

[0029] Additionally, the method may further comprise operating the first coating source as an other magnetron with inert gas, and operating the magnetron with at least one of the inert gas and reactive gas. In such implementations, the inert gas comprises argon and/or the reactive gas comprises at least one of nitrogen, oxygen, and methane.

[0030] In further embodiments, the area density of the auxiliary substrate is determined after the coating of the substrate. Moreover, the determining of the area density of the auxiliary substrate may comprise x-ray fluorescence.

[0031] In even further embodiments, the method comprises operating the magnetron with DC voltage or pulsed DC voltage. Also, the cathode may comprise several cathodes and the method may further comprise operating the magnetron with the several cathodes with a frequency of approximately 10 kHz to approximately 100 kHz.

[0032] Additionally, the coating of the substrate may comprises depositing an other layer on the substrate. The other layer may comprise titanium dioxide.

BRIEF DESCRIPTION OF THE DRAWINGS

[0033] The invention is described below by way of example on the basis of one ~~Fig.~~Figure, in which:

[0034] Fig. 1 shows the diagrammatic structure of a magnetron coating module according to the present invention.

DETAILED DESCRIPTION OF THE PRESENT INVENTION

[0035] ~~In the center the Fig.~~ The Figure shows a cylindrical auxiliary substrate 2 that rotates about its longitudinal axis. The substrate 1 to be coated is arranged below the cylindrical auxiliary substrate 2. This substrate 1 can be, e.g., architectural glass. The substrate 1 is moved through under the coating system. Plasma is ignited through a voltage applied to the auxiliary substrate 2, in the area 3 between the auxiliary substrate 2 and the substrate 1. The auxiliary substrate 2 thus forms a rod cathode from which material is sputtered off which coats the substrate 1 switched as an anode. A mixture of inert and reactive gas is located in the area 3, which permits the deposit of a multi-component layer. A planar magnetron 5 in a shield 4 is located on the opposite side of the auxiliary substrate 2. In this case, the auxiliary substrate 2 is switched as an anode that is coated with material of the planar sputtering cathode of the planar magnetron 5 in the plasma area 7. The gas phase in area 7 contains exclusively inert gas so that the deposition rate in area 7 can be determined from the known sputtering rates and the electric parameters. The coating rate on the substrate 1 results from the mass balance on the auxiliary substrate 2. In addition to the known coating rate in the area 7, the area density after the sputtering process in area 3 is determined~~required to this end as well~~. To this end, a device for determining the x-ray fluorescence 6 is located behind the area (i.e., plasma zone) 3. The device 6 thereby contains an x-ray source for irradiating the auxiliary substrate 2 and a photodetector for determining the x-ray radiation reflected from the auxiliary substrate.